

R1LV0216BSB

2Mb Advanced LPSRAM (128k word x 16bit)

R10DS0051EJ0100
Rev.1.00
2011.03.30

Description

The R1LV0216BSB is a family of low voltage 2-Mbit static RAMs organized as 131,072-word by 16-bit, fabricated by Renesas's high-performance 0.15um CMOS and TFT technologies. The R1LV0216BSB has realized higher density, higher performance and low power consumption. The R1LV0216BSB is suitable for memory applications where a simple interfacing, battery operating and battery backup are the important design objectives. The R1LV0216BSB has been packaged in 44-pin TSOP.

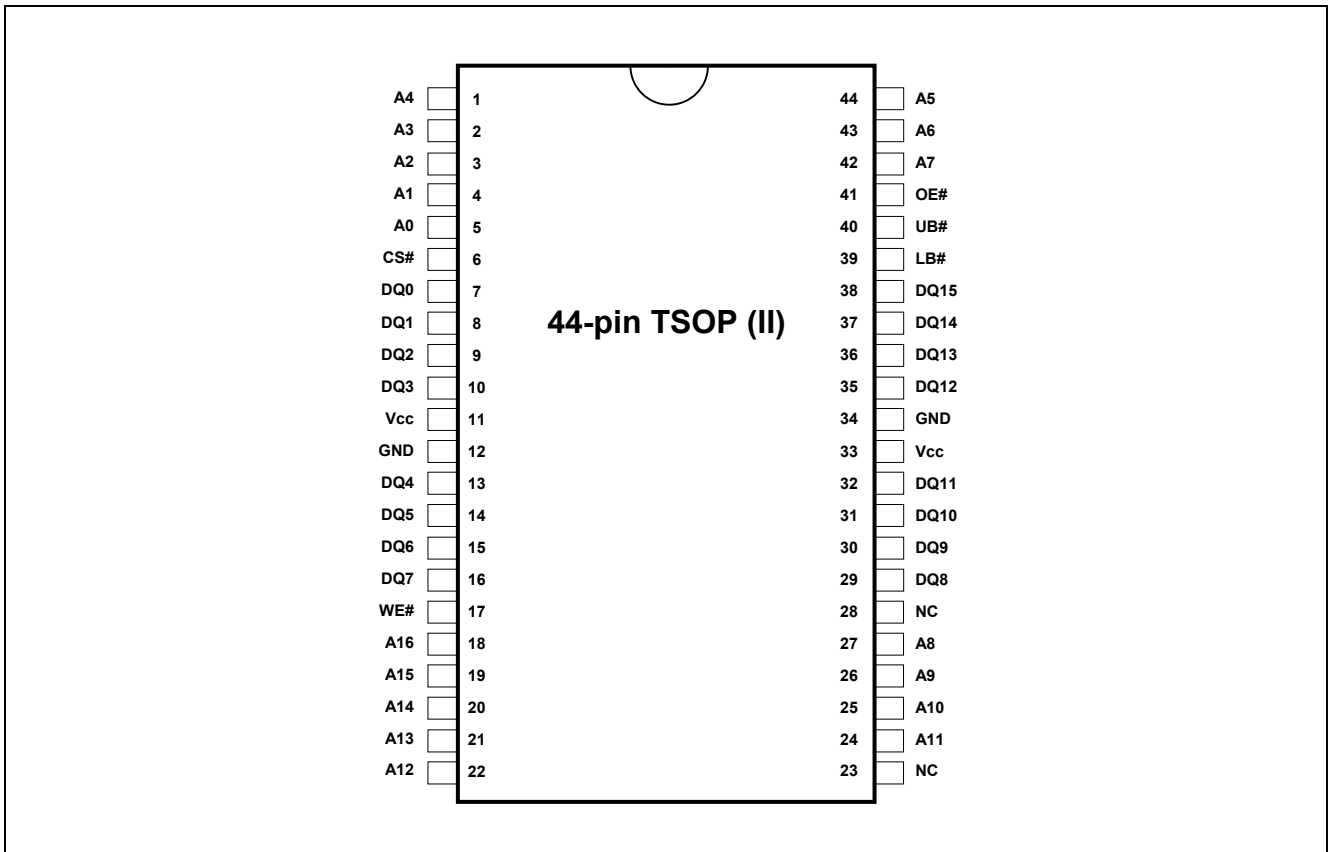
Features

- Single 2.7~3.6V power supply
- Small stand-by current: 1μA (3.0V, typical)
- No clocks, No refresh
- All inputs and outputs are TTL compatible.
- Easy memory expansion by CS#, LB# and UB#
- Common Data I/O
- Three-state outputs: OR-tie Capability
- OE# prevents data contention on the I/O bus

Ordering Information

Orderable Part Name	Access time	Temperature Range	Package	Shipping Container	Quantity
R1LV0216BSB-5SR#B0	55 ns	0 ~ +70°C	400-mil 44pin plastic TSOP (II) (normal-bend type)	Tray	Max. 135pcs/Tray Max. 1080pcs/Inner Box
R1LV0216BSB-5SI#B0		-40 ~ +85°C			
R1LV0216BSB-7SR#B0	70 ns	0 ~ +70°C			
R1LV0216BSB-7SI#B0		-40 ~ +85°C			
R1LV0216BSB-5SR#S0	55 ns	0 ~ +70°C	PTSB0044GD-B (44P3F-B)	Embossed tape	1000pcs/Reel
R1LV0216BSB-5SI#S0		-40 ~ +85°C			
R1LV0216BSB-7SR#S0	70 ns	0 ~ +70°C			
R1LV0216BSB-7SI#S0		-40 ~ +85°C			

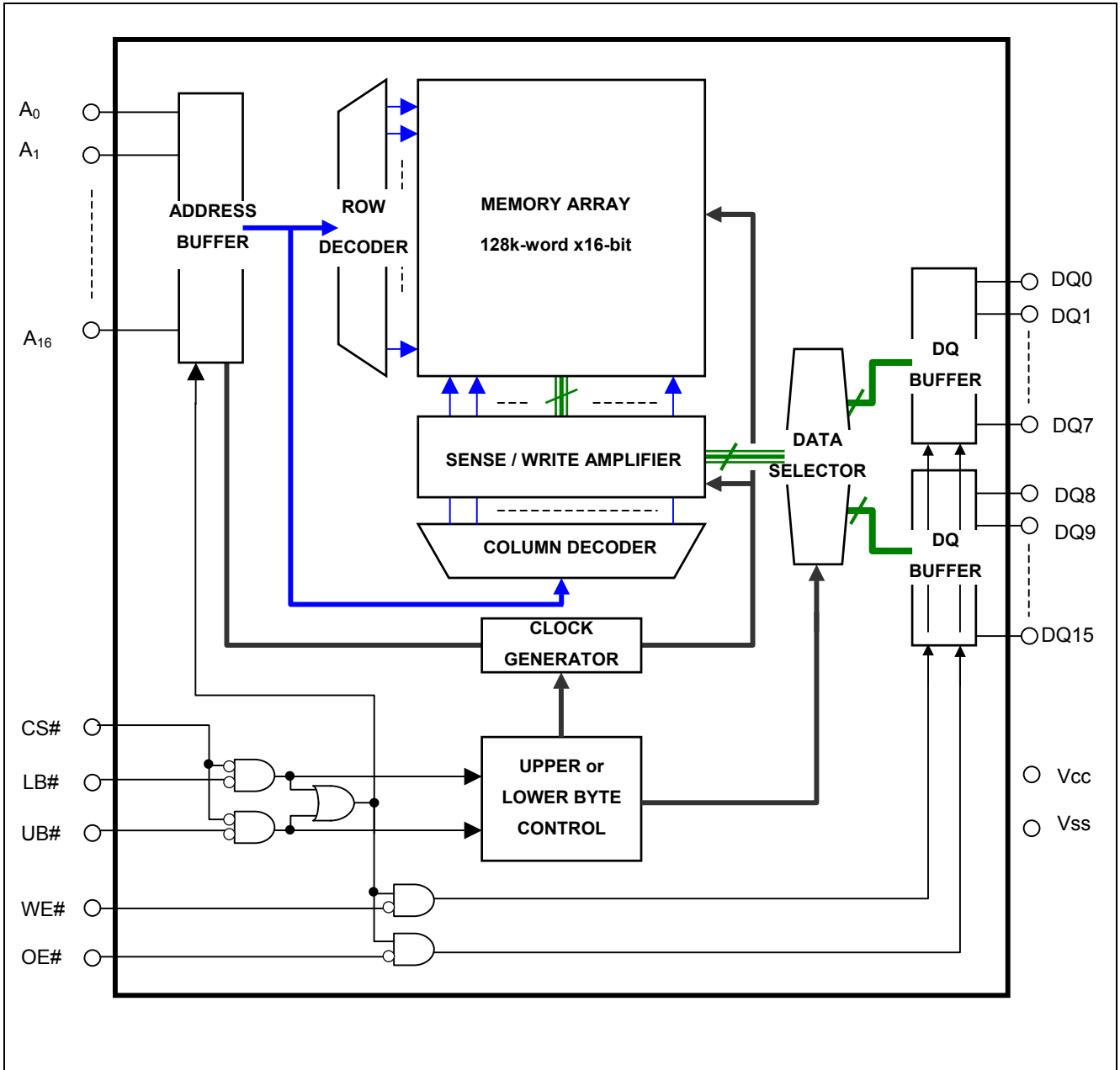
Pin Arrangement



Pin Description

Pin name	Function
Vcc	Power supply
Vss	Ground
A0 to A16	Address input
DQ0 to DQ15	Data input/output
CS#	Chip select 1
WE#	Write enable
OE#	Output enable
LB#	Lower byte enable
UB#	Upper byte enable
NC	Non connection

Block Diagram



Operation Table

CS#	LB#	UB#	WE#	OE#	DQ0~7	DQ8~15	Operation
H	X	X	X	X	High-Z	High-Z	Stand-by
X	H	H	X	X	High-Z	High-Z	Stand-by
L	L	H	L	X	Din	High-Z	Write in lower byte
L	L	H	H	L	Dout	High-Z	Read in lower byte
L	L	H	H	H	High-Z	High-Z	Output disable
L	H	L	L	X	High-Z	Din	Write in upper byte
L	H	L	H	L	High-Z	Dout	Read in upper byte
L	H	L	H	H	High-Z	High-Z	Output disable
L	L	L	L	X	Din	Din	Word write
L	L	L	H	L	Dout	Dout	Word read
L	L	L	H	H	High-Z	High-Z	Output disable

Note 1. H: V_{IH} L: V_{IL} X: V_{IH} or V_{IL}

Absolute Maximum

Parameter	Symbol	Value	unit
Power supply voltage relative to Vss	Vcc	-0.5 to +4.6	V
Terminal voltage on any pin relative to Vss	V_T	-0.5^{*1} to $V_{cc}+0.5^{*2}$	V
Power dissipation	P_T	0.7	W
Operation temperature	T_{opr}^{*3}	R Ver.	0 to +70
		I Ver.	-40 to +85
Storage temperature range	Tstg	-65 to 150	°C
Storage temperature range under bias	T_{bias}^{*3}	R Ver.	0 to +70
		I Ver.	-40 to +85

- Note
1. $-3.0V$ for pulse $\leq 30ns$ (full width at half maximum)
 2. Maximum voltage is +4.6V.
 3. Ambient temperature range depends on R/I-version. Please see table on page 1.

DC Operating Conditions

Parameter		Symbol	Min.	Typ.	Max.	Unit	Note
Supply voltage		V _{CC}	2.7	3.0	3.6	V	
		V _{SS}	0	0	0	V	
Input high voltage		V _{IH}	2.2	-	V _{CC} +0.3	V	
Input low voltage		V _{IL}	-0.3	-	0.6	V	1
Ambient temperature range	R Ver.	T _a	0	-	+70	°C	2
	I Ver.		-40	-	+85	°C	2

Note 1. -3.0V for pulse ≤ 30ns (full width at half maximum)

2. Ambient temperature range depends on R/I-version. Please see table on page 1.

DC Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test conditions	
Input leakage current	I _{LI}	-	-	1	μA	V _{in} = V _{SS} to V _{CC}	
Output leakage current	I _{LO}	-	-	1	μA	CS# = LB# = UB# = V _{IH} or OE# = V _{IH} , V _{I/O} = V _{SS} to V _{CC}	
Average operating current	I _{CC1}	-	15	25	mA	Min. cycle, duty = 100%, I _{I/O} = 0mA CS# = V _{IL} , Others = V _{IH} /V _{IL}	
	I _{CC2}	-	2	5	mA	Cycle = 1μs, duty = 100%, I _{I/O} = 0mA CS# ≤ 0.2V, V _{IH} ≥ V _{CC} -0.2V, V _{IL} ≤ 0.2V	
Standby current	I _{SB}	-	-	0.5	mA	(1) CS# = V _{IH} , Others = V _{IH} /V _{IL} or (2) LB# = UB# = V _{IH} , Others = V _{IH} /V _{IL}	
Standby current	I _{SB1}	-	1 ^{*1}	2	μA	~+25°C	V _{in} = V _{SS} to V _{CC} (1) CS# ≥ V _{CC} -0.2V or (2) LB# = UB# ≥ V _{CC} -0.2V, CS# ≤ 0.2V
		-	-	3	μA	~+40°C	
		-	-	8	μA	~+70°C	
		-	-	10	μA	~+85°C	
Output high voltage	V _{OH}	2.4	-	-	V	I _{OH} = -0.5mA	
	V _{OH2}	V _{CC} - 0.5	-	-	V	I _{OH} = -0.05mA	
Output low voltage	V _{OL}	-	-	0.4	V	I _{OL} = 2mA	

Note 1. Typical parameter indicates the value for the center of distribution at 3.0V (T_a = 25°C), and not 100% tested.

Capacitance

($V_{CC} = 2.7V \sim 3.6V$, $f = 1MHz$, $T_a = 0 \sim +70^{\circ}C / -40 \sim +85^{\circ}C^{*2}$)

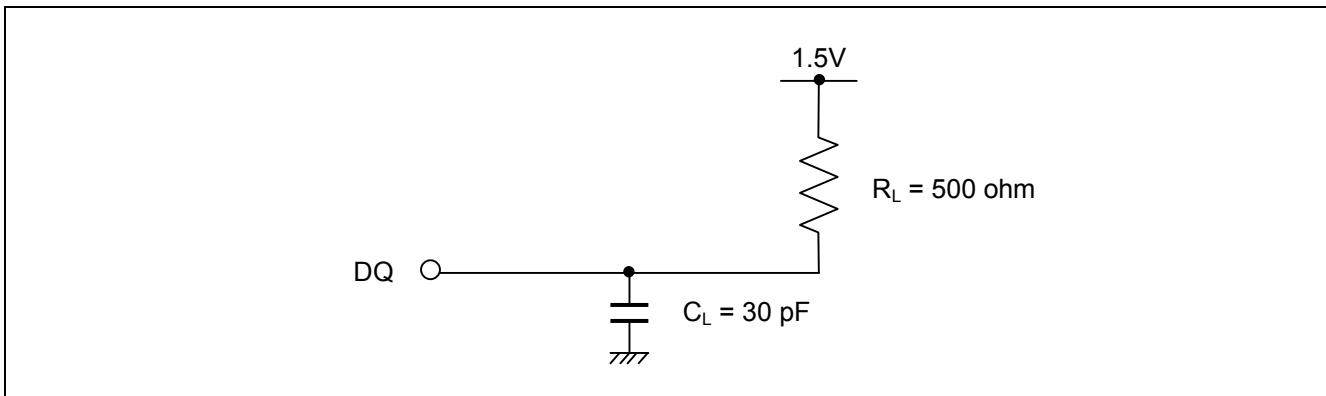
Parameter	Symbol	Min.	Typ.	Max.	Unit	Test conditions	Note
Input capacitance	C_{in}	-	-	8	pF	$V_{in} = 0V$	1
Input / output capacitance	$C_{I/O}$	-	-	10	pF	$V_{I/O} = 0V$	1

- Note
1. This parameter is sampled and not 100% tested.
 2. Ambient temperature range depends on R/I-version. Please see table on page 1.

AC Characteristics

Test Conditions ($V_{CC} = 2.7V \sim 3.6V$, $T_a = 0 \sim +70^{\circ}C / -40 \sim +85^{\circ}C^{*1}$)

- Input pulse levels: $V_{IL} = 0.4V$, $V_{IH} = 2.4V$
- Input rise and fall time: 5ns
- Input and output timing reference level: 1.5V
- Output load: See figures (Including scope and jig)



- Note
1. Ambient temperature range depends on R/I-version. Please see table on page 1.

Read Cycle

Parameter	Symbol	R1LV0216BSB-5S*		R1LV0216BSB-7S*		Unit	Note
		Min.	Max.	Min.	Max.		
Read cycle time	t _{RC}	55	-	70	-	ns	
Address access time	t _{AA}	-	55	-	70	ns	
Chip select access time	t _{ACS}	-	55	-	70	ns	
Output enable to output valid	t _{OE}	-	30	-	35	ns	
Output hold from address change	t _{OH}	10	-	10	-	ns	
LB#, UB# access time	t _{BA}	-	55	-	70	ns	
Chip select to output in low-Z	t _{CLZ}	10	-	10	-	ns	2,3
LB#, UB# enable to low-Z	t _{BLZ}	10	-	10	-	ns	2,3
Output enable to output in low-Z	t _{OLZ}	5	-	5	-	ns	2,3
Chip deselect to output in high-Z	t _{CHZ}	0	20	0	25	ns	1,2,3
LB#, UB# disable to high-Z	t _{BHZ}	0	20	0	25	ns	1,2,3
Output disable to output in high-Z	t _{OHZ}	0	20	0	25	ns	1,2,3

Write Cycle

Parameter	Symbol	R1LV0216BSB-5S*		R1LV0216BSB-7S*		Unit	Note
		Min.	Max.	Min.	Max.		
Write cycle time	t_{WC}	55	-	70	-	ns	
Address valid to end of write	t_{AW}	50	-	55	-	ns	
Chip select to end of write	t_{CW}	50	-	55	-	ns	5
Write pulse width	t_{WP}	45	-	50	-	ns	4
LB#, UB# valid to end of write	t_{BW}	50	-	55	-	ns	
Address setup time	t_{AS}	0	-	0	-	ns	6
Write recovery time	t_{WR}	0	-	0	-	ns	7
Data to write time overlap	t_{DW}	25	-	30	-	ns	
Data hold from write time	t_{DH}	0	-	0	-	ns	
Output enable from end of write	t_{OW}	5	-	5	-	ns	2
Output disable to output in high-Z	t_{OHZ}	0	20	0	25	ns	1,2
Write to output in high-Z	t_{WHZ}	0	20	0	25	ns	1,2

- Note
- t_{CHZ} , t_{OHZ} and t_{WHZ} are defined as the time at which the outputs achieve the open circuit conditions and are not referred to output voltage levels.
 - This parameter is sampled and not 100% tested.
 - At any given temperature and voltage condition, t_{HZ} max is less than t_{LZ} min both for a given device and from device to device.
 - A write occurs during the overlap of a low CS#, a low WE# and a low LB# or a low UB#.

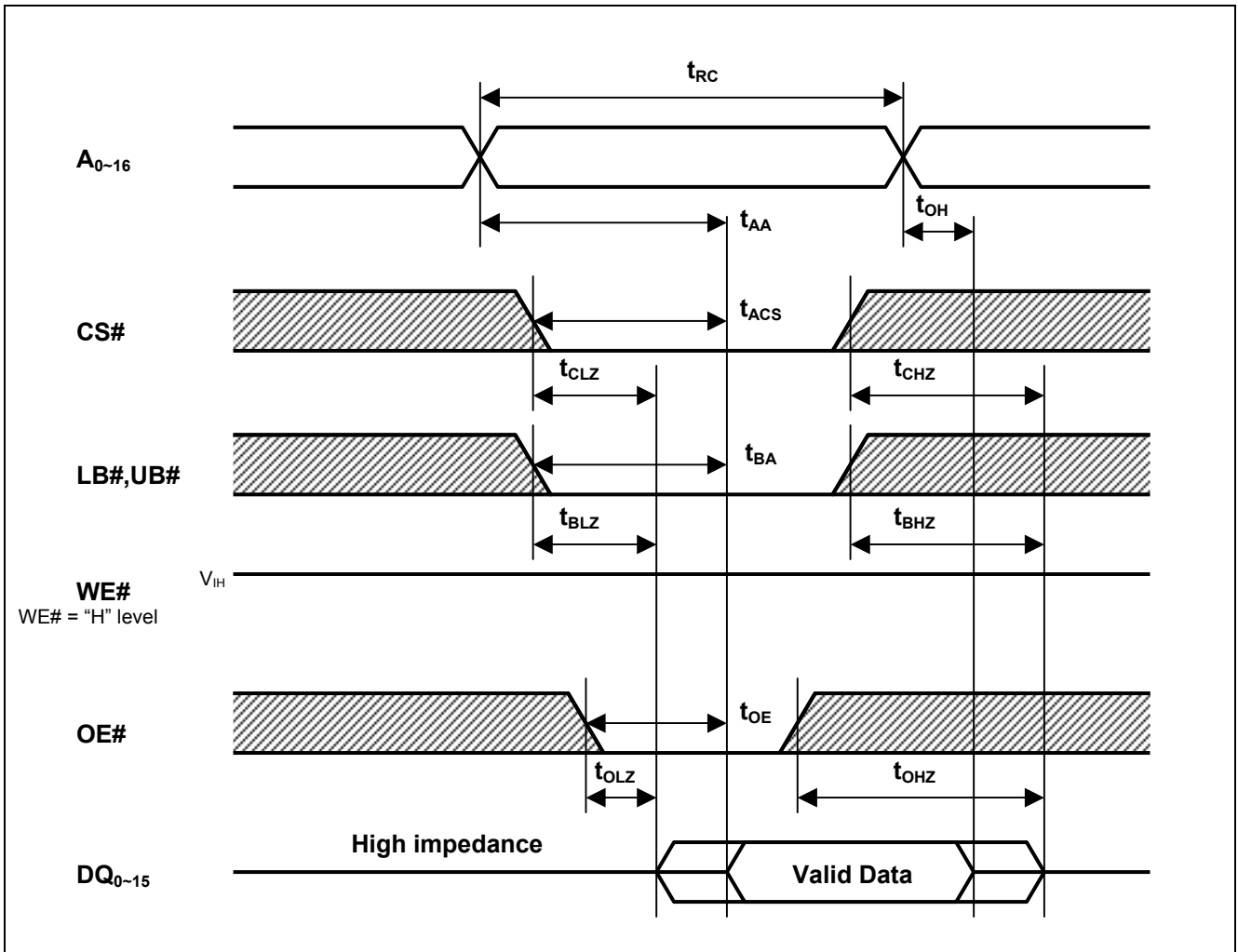
A write begins at the latest transition among CS# going low, WE# going low and LB# going low or UB# going low.

A write ends at the earliest transition among CS# going high, WE# going high and LB# going high or UB# going high.

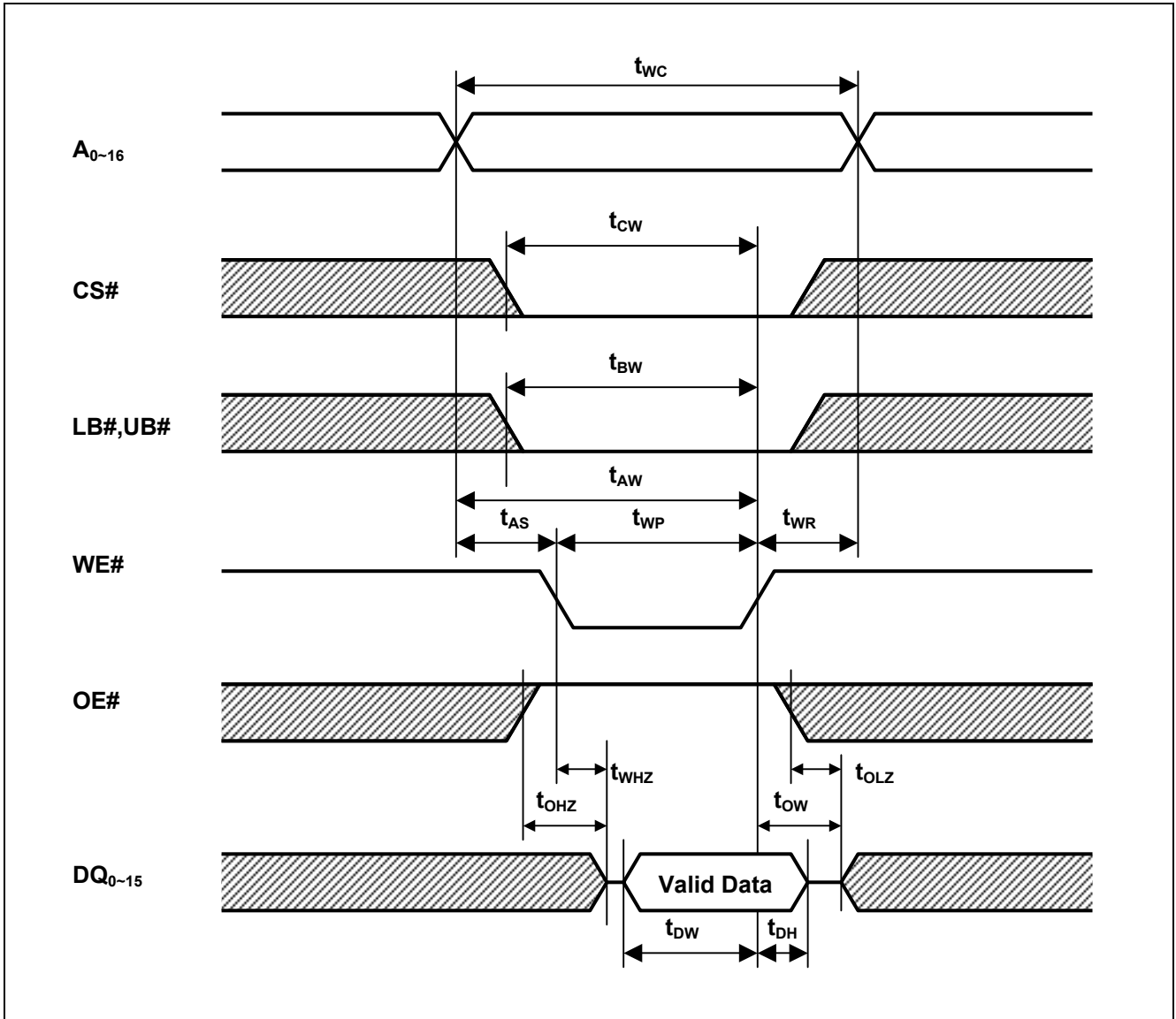
t_{WP} is measured from the beginning of write to the end of write.
 - t_{CW} is measured from the later of CS# going low to end of write.
 - t_{AS} is measured the address valid to the beginning of write.
 - t_{WR} is measured from the earliest of CS#, WE#, LB# or UB# going high to the end of write cycle.
 - Don't apply inverted phase signal externally when DQ pin is output mode.

Timing Waveforms

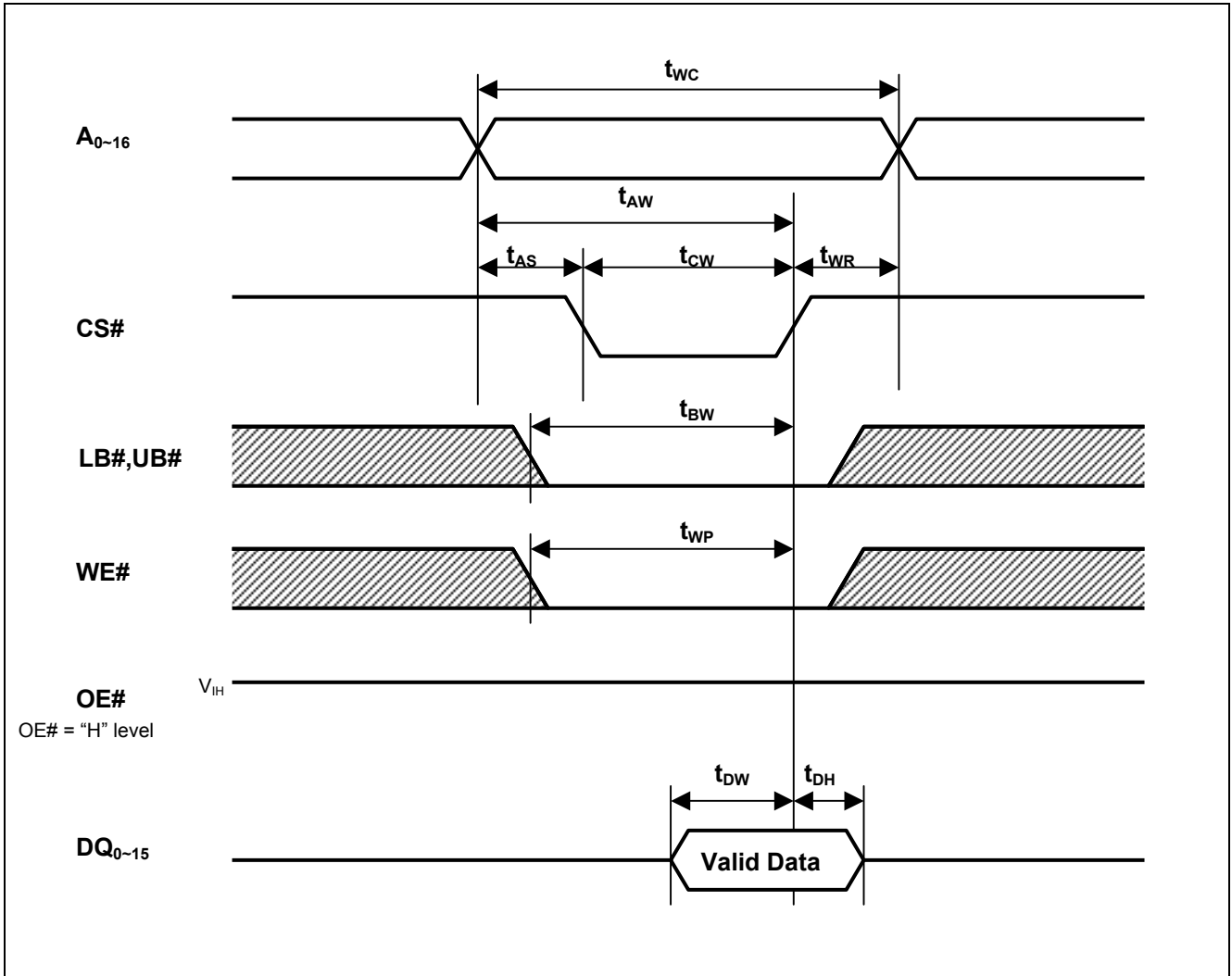
Read Cycle



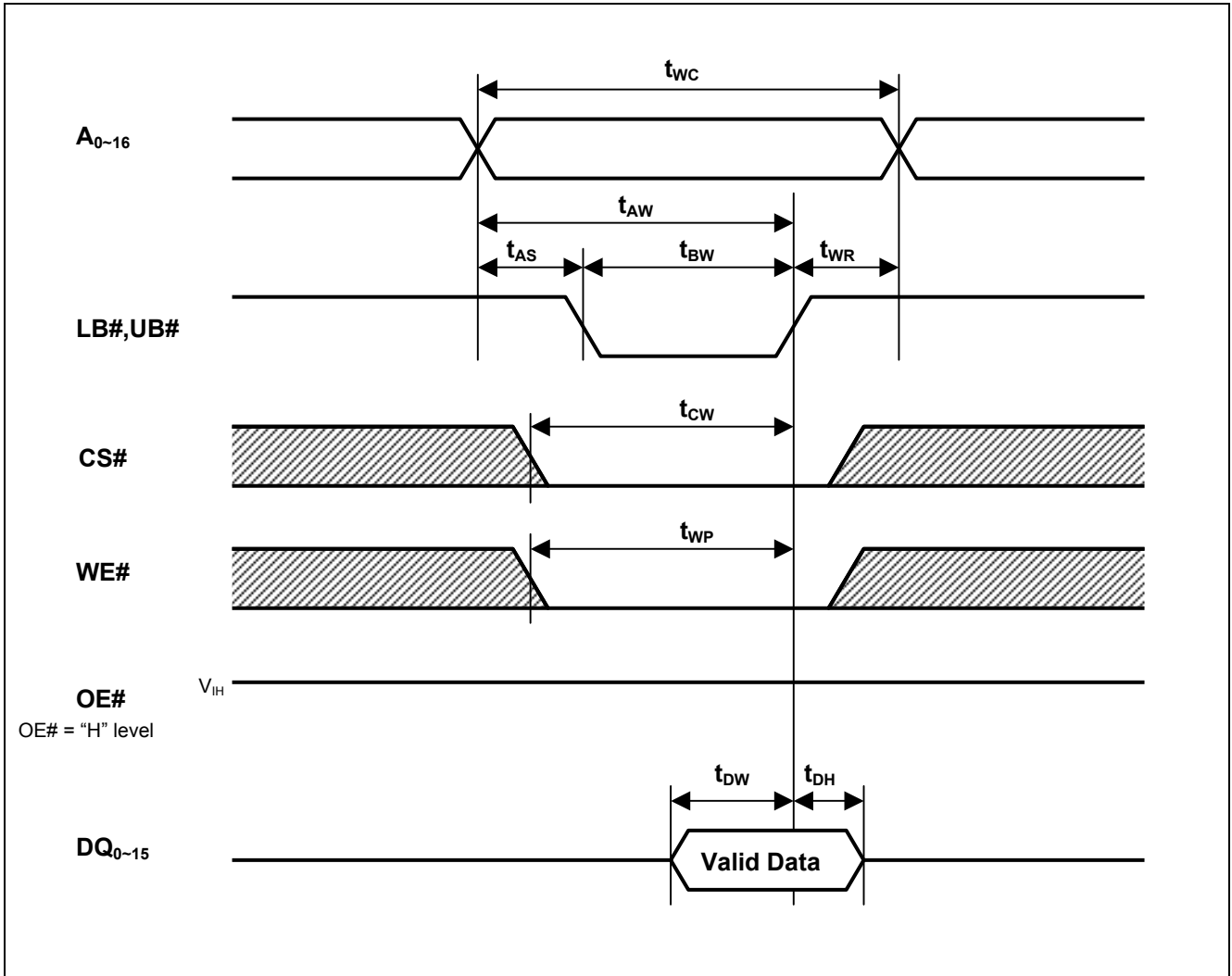
Write Cycle (1) (WE# CLOCK)



Write Cycle (2) (CS1#, CS2 CLOCK)



Write Cycle (3) (LB#, UB# CLOCK)



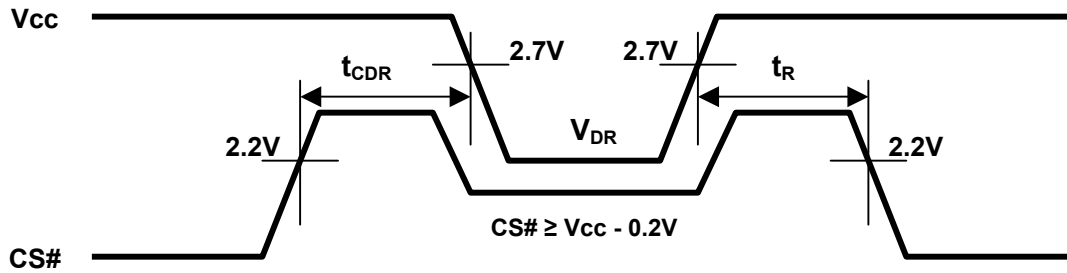
Low Vcc Data Retention Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test conditions ²	
V _{CC} for data retention	V _{DR}	2.0	-	3.6	V	V _{in} ≥ 0V (1) CS# ≥ V _{CC} -0.2V or (2) LB# = UB# ≥ V _{CC} -0.2V, CS# ≤ 0.2V	
Data retention current	I _{CCDR}	-	1 ^{*1}	2	μA	~+25°C	V _{CC} =3.0V, V _{in} ≥ 0V (1) CS# ≥ V _{CC} -0.2V or (2) LB# = UB# ≥ V _{CC} -0.2V, CS# ≤ 0.2V
		-	-	3	μA	~+40°C	
		-	-	8	μA	~+70°C	
		-	-	10	μA	~+85°C	
Chip deselect to data retention time	t _{CDR}	0	-	-	ns	See retention waveform.	
Operation recovery time	t _R	5	-	-	ms		

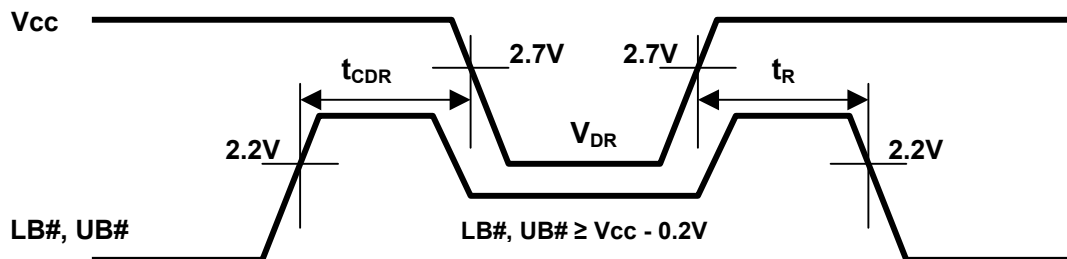
- Note
1. Typical parameter indicates the value for the center of distribution at 3.0V (T_a = 25°C), and not 100% tested.
 2. CS# controls address buffer, WE# buffer, OE# buffer, LB# buffer, UB# buffer and Din buffer. If CS# controls data retention mode, V_{in} levels (address, WE#, OE#, LB#, UB#, DQ) can be in the high impedance state.

Low Vcc Data Retention Timing Waveforms

(1) CS# Controlled



(2) LB#, UB# Controlled



Revision History	R1LV0216BSB Data Sheet
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Rev.	Date	Description	
		Page	Summary
1.00	2011.03.30	-	First Edition issued

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Renesas Electronics America Inc.
2880 Scott Boulevard Santa Clara, CA 95050-2554, U.S.A.
Tel: +1-408-586-6000, Fax: +1-408-586-6130

Renesas Electronics Canada Limited
1101 Nicholson Road, Newmarket, Ontario L3Y 9C3, Canada
Tel: +1-905-898-5441, Fax: +1-905-898-3220

Renesas Electronics Europe Limited
Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K.
Tel: +44-1628-585-100, Fax: +44-1628-585-900

Renesas Electronics Europe GmbH
Arcadiastrasse 10, 40472 Düsseldorf, Germany
Tel: +49-211-65030, Fax: +49-211-6503-1327

Renesas Electronics (China) Co., Ltd.
7th Floor, Quantum Plaza, No.27 ZhiChunLu Haidian District, Beijing 100083, P.R.China
Tel: +86-10-8235-1155, Fax: +86-10-8235-7679

Renesas Electronics (Shanghai) Co., Ltd.
Unit 204, 205, AZIA Center, No.1233 Lujiazui Ring Rd., Pudong District, Shanghai 200120, China
Tel: +86-21-5877-1818, Fax: +86-21-6887-7858 / -7898

Renesas Electronics Hong Kong Limited
Unit 1601-1613, 16/F., Tower 2, Grand Century Place, 193 Prince Edward Road West, Mongkok, Kowloon, Hong Kong
Tel: +852-2886-9318, Fax: +852 2886-9022/9044

Renesas Electronics Taiwan Co., Ltd.
13F, No. 363, Fu Shing North Road, Taipei, Taiwan
Tel: +886-2-8175-9600, Fax: +886 2-8175-9670

Renesas Electronics Singapore Pte. Ltd.
1 HarbourFront Avenue, #06-10, Keppel Bay Tower, Singapore 098632
Tel: +65-6213-0200, Fax: +65-6276-8001

Renesas Electronics Malaysia Sdn.Bhd.
Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No. 18, Jin Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia
Tel: +60-3-7955-9390, Fax: +60-3-7955-9510

Renesas Electronics Korea Co., Ltd.
11F., Samik Lavied' or Bldg., 720-2 Yeoksam-Dong, Kangnam-Ku, Seoul 135-080, Korea
Tel: +82-2-558-3737, Fax: +82-2-558-5141